

## ABSTRACT OF THE DISCLOSURE

Semiconductor light emitting devices are provided. The semiconductor light emitting device includes a base body, a selection mask having a stripe-shaped opening portion, the selection mask being formed on the base body, a semiconductor layer  
5 formed by selective growth from the opening portion in such a manner as to have a ridge line substantially parallel to long-sides of the opening portion, and a first conductive type cladding layer, an active layer, and a second conductive type cladding layer, which are formed on the semiconductor layer.